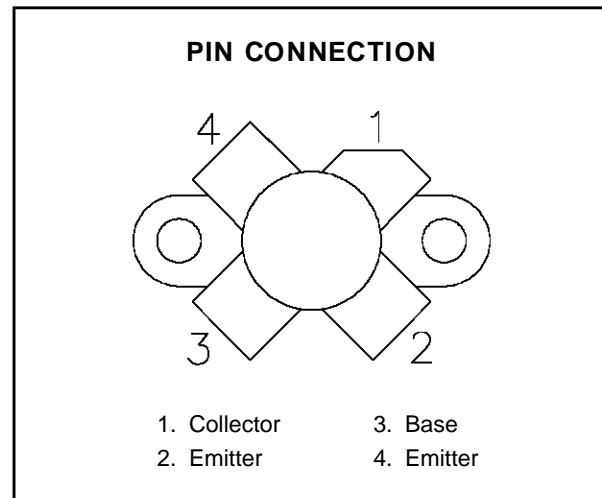
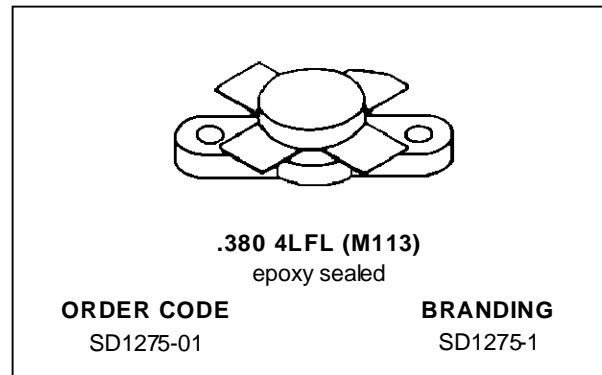


**RF & MICROWAVE TRANSISTORS  
VHF MOBILE APPLICATIONS**

- 160 MHz
- 13.6 VOLTS
- COMMON EMITTER
- P<sub>OUT</sub> = 40 W MIN. WITH 9.0 dB GAIN


**DESCRIPTION**

The SD1275-01 is a 13.6 V Class C epitaxial silicon NPN planar transistor designed primarily for VHF communications. The SD1275-01 utilizes an emitter ballasted die geometry to withstand severe load mismatch conditions.

**ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	36	V
V <sub>CEO</sub>	Collector-Emitter Voltage	16	V
V <sub>CES</sub>	Collector-Emitter Voltage	36	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>c</sub>	Device Current	8.0	A
P <sub>DISS</sub>	Power Dissipation	70	W
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	- 65 to +150	°C

**THERMAL DATA**

R <sub>TH(j-c)</sub>	Junction-Case Thermal Resistance	1.2	°C/W
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# SD1275-01

## ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

### STATIC

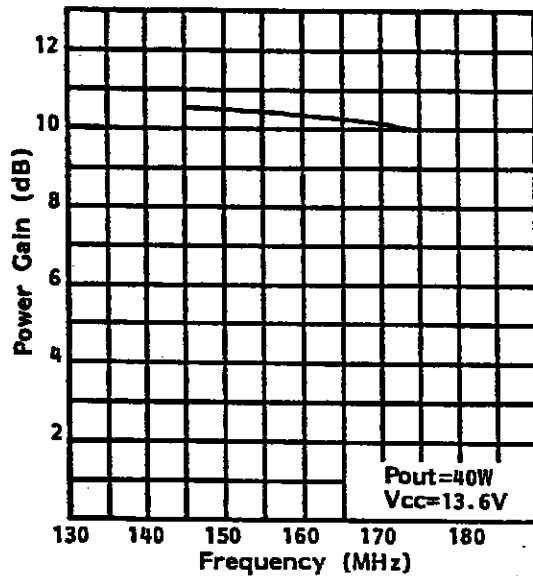
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV <sub>CES</sub>	I <sub>C</sub> = 15mA	V <sub>BE</sub> = 0mA	36	—	—	V
BV <sub>CEO</sub>	I <sub>C</sub> = 50mA	I <sub>B</sub> = 0mA	16	—	—	V
BV <sub>EBO</sub>	I <sub>E</sub> = 5mA	I <sub>C</sub> = 0mA	4.0	—	—	V
I <sub>CBO</sub>	V <sub>CB</sub> = 15V	I <sub>E</sub> = 0mA	—	—	5	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5V	I <sub>C</sub> = 250mA	20	—	—	—

### DYNAMIC

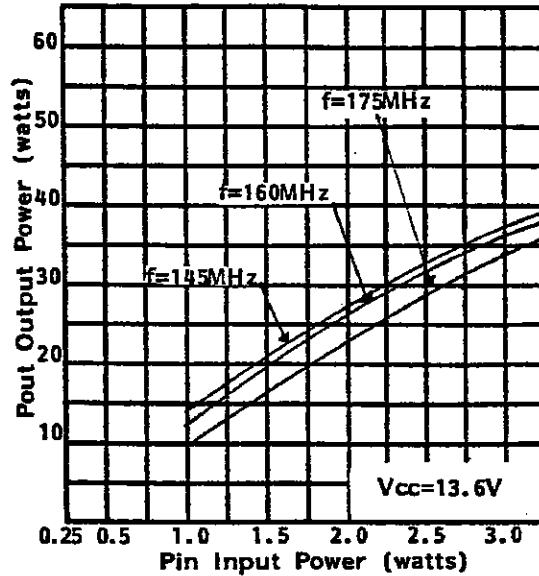
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P <sub>OUT</sub>	f = 160 MHz	P <sub>IN</sub> = 5.0 W	V <sub>CE</sub> = 13.6 V	40	—	—	W
G <sub>P</sub>	f = 160 MHz	P <sub>IN</sub> = 5.0 W	V <sub>CE</sub> = 13.6 V	9	—	—	dB
C <sub>OB</sub>	f = 1 MHz	V <sub>CB</sub> = 15 V		—	95	—	pF

### TYPICAL PERFORMANCE

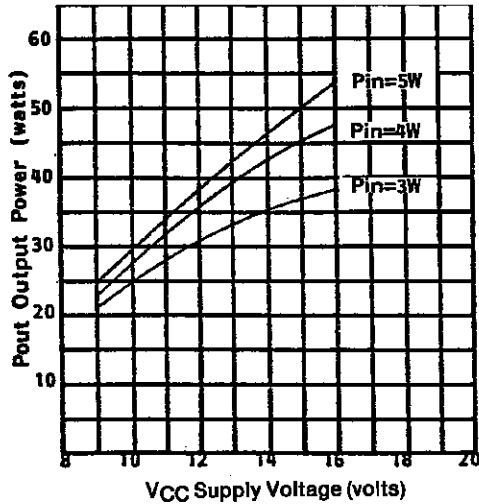
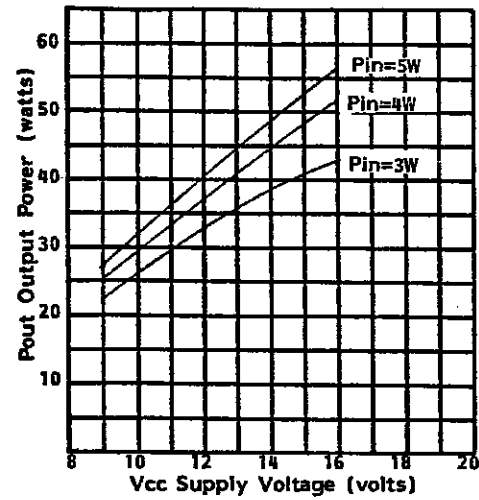
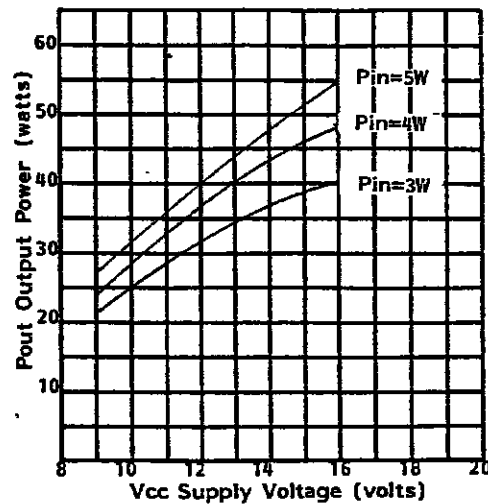
POWER GAIN vs FREQUENCY



POWER OUTPUT vs POWER INPUT



## TYPICAL PERFORMANCE (cont'd)

POWER OUTPUT vs SUPPLY VOLTAGE  
(175 MHz)POWER OUTPUT vs SUPPLY VOLTAGE  
(145 MHz)POWER OUTPUT vs SUPPLY VOLTAGE  
(160 MHz)

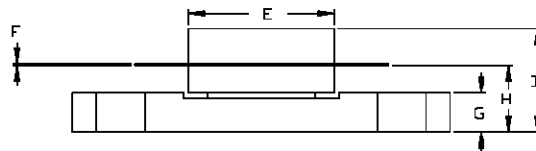
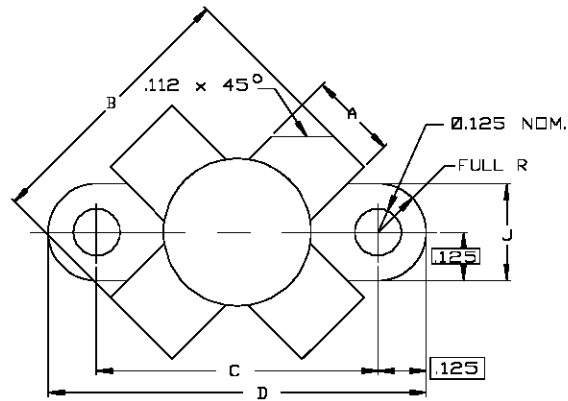
## IMPEDANCE DATA

FREQ.	Z <sub>IN</sub> (Ω)	Z <sub>CL</sub> (Ω)
160 MHz	1.0 + j 0.4	2.3 + j 0.1

P<sub>IN</sub> = 3.0 W  
V<sub>CE</sub> = 12.5 V

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0113



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.785/19,94	
C	.720/18,29	.730/18,54
D	.970/24,64	.980/24,89
E		.385/9,78
F	.004/0,10	.006/0,15
G	.085/2,16	.105/2,67
H	.160/4,06	.190/4,57
I		.280/7,11
J	.240/6,10	.255/6,48

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